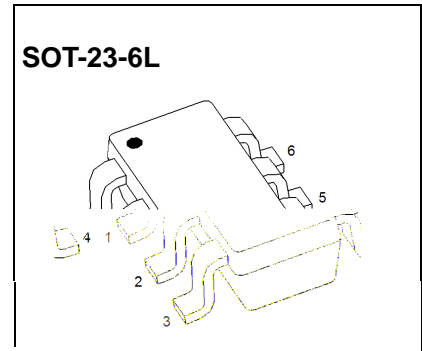




SOT-23-6L Plastic-Encapsulate

CJL2623 Dual P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-30V	130mΩ@-10V	-3A
	180mΩ@-4.5V	



FEATURE

- TrenchFET Power MOSFET
- Low Gate Charge
- Low On-resistance
- Surface Mount Package

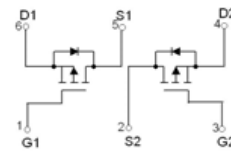
APPLICATION

- DC/DC converter
- Load switch for portable devices
- Commercial-industrial applications

MARKING:



Equivalent Circuit



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-3	A
Pulsed Drain Current (note 1)	I_{DM}	-20	A
Power Dissipation (note 2)	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ 150	$^{\circ}C$

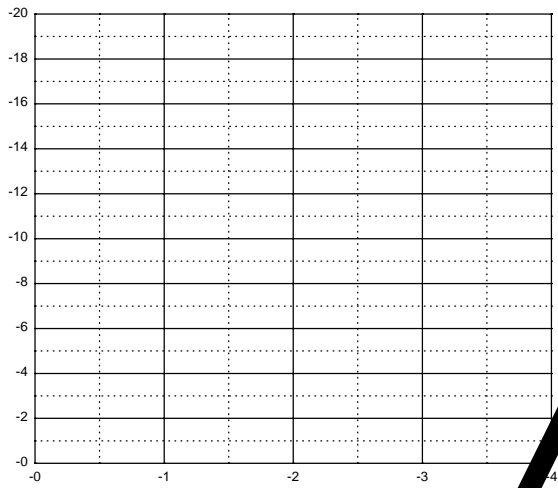
- Notes :**
1. Pulse width limited by Max.junction temperature.
 - 2.Per element must not be exceeded

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

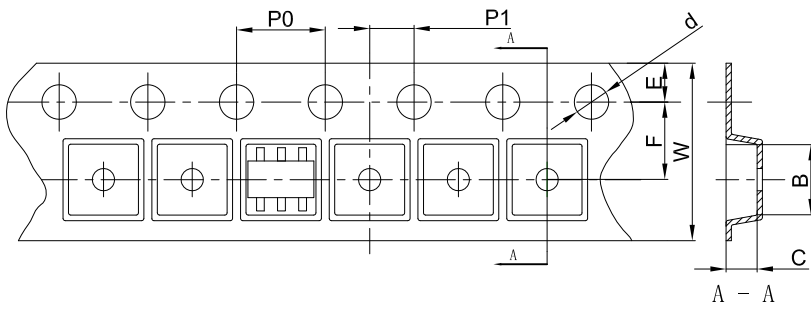
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1		-3	V
Drain-source on-resistance (note 3)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -3A$			130	$m\Omega$
		$V_{GS} = -4.5V, I_D = -2A$			180	$m\Omega$
Forward tranconductance	g_{FS}	$V_{DS} = -5V, I_D = -2A$		2		S
Diode forward voltage (note 3)	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1.2	V
DYNAMIC PARAMETERS (note 4)						
Input Capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1MHz$			240	pF
Output Capacitance	C_{oss}			42		pF
Reverse Transfer Capacitance	C_{rss}			32		pF
SWITCHING PARAMETERS (note 3,4)						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15V, V_{GS} = -10V, I_D = -1A$ $R_D = 15\Omega, R_G = 3.3\Omega$		5		ns
Turn-on rise time	t_r			6		ns
Turn-off delay time	$t_{d(off)}$			15		ns
Turn-off fall time	t_f			3		ns
Total Gate Charge	Q_g	$V_{DS} = -24V, V_{GS} = -4.5V, I_D = -2A$			4.5	nC

Typical Characteristics



JCET reserve the right to make modifications.

NOTICE



Packaging Description:

SOT-23-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3